

Development of large-area UFSD sensors for the CMS MIP Timing Detector

R. Arcidiacono on behalf of the CMS collaboration

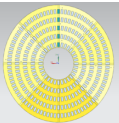
UPO & INFN Torino



TREDI 2019

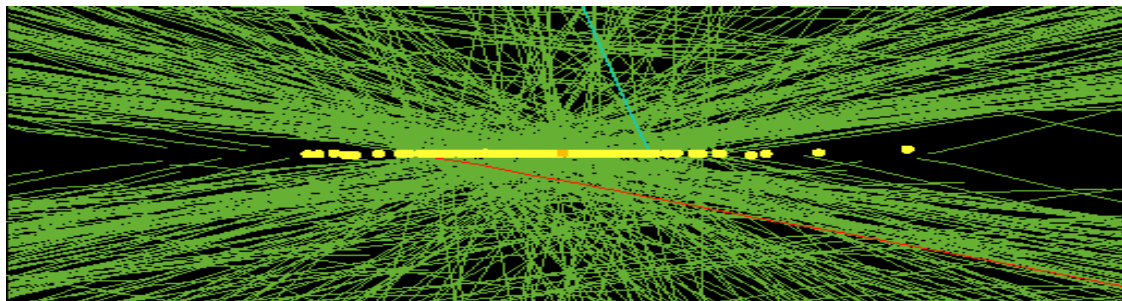
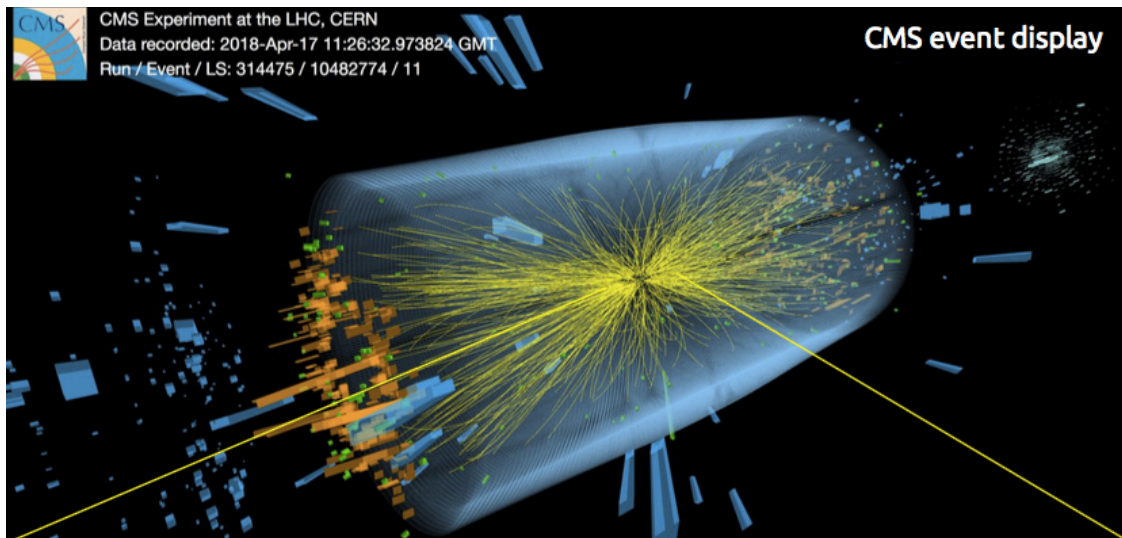
14th Trento Workshop on Advanced Silicon Radiator Detectors

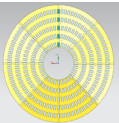
Trento, from Monday 25 February to Wednesday 27 February 2019



LHC upgrade: the High Luminosity Challenge

	Inst. Lumi ($\text{cm}^{-2}\text{s}^{-1}$)	Peak pileup (PU)
LHC	1.7×10^{34}	60
HL-LHC	$5-7.5 \times 10^{34}$	140-200

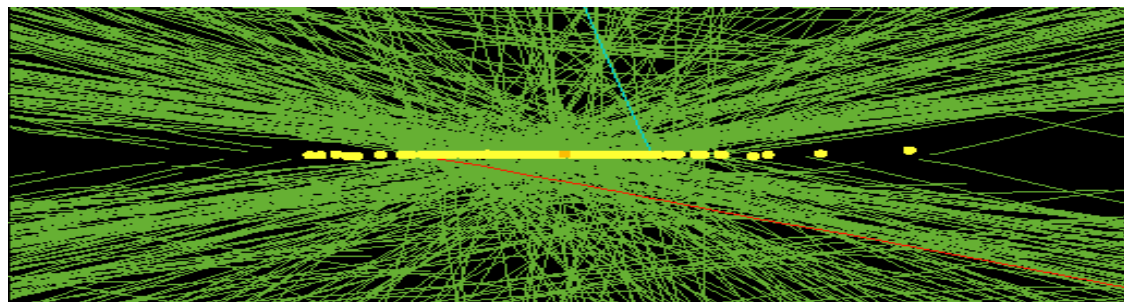
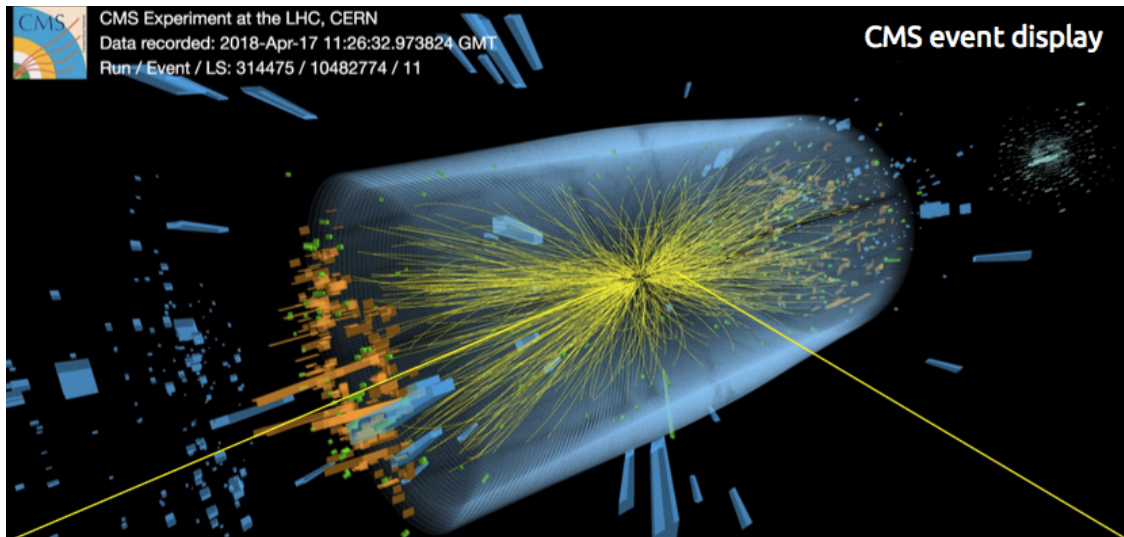
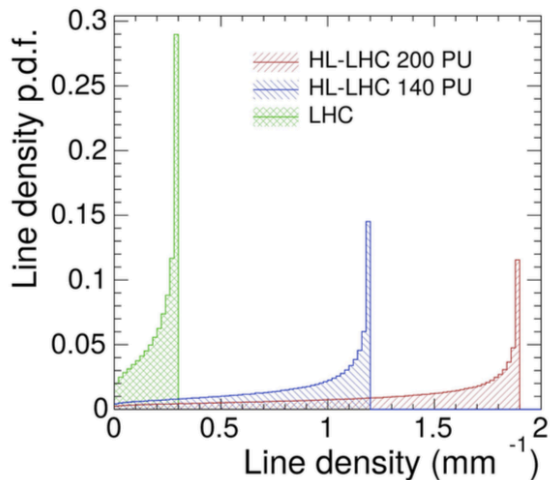


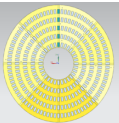


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- Up to **5x higher vertex density**
- Current track-vertex compatibility cut is @ 1mm



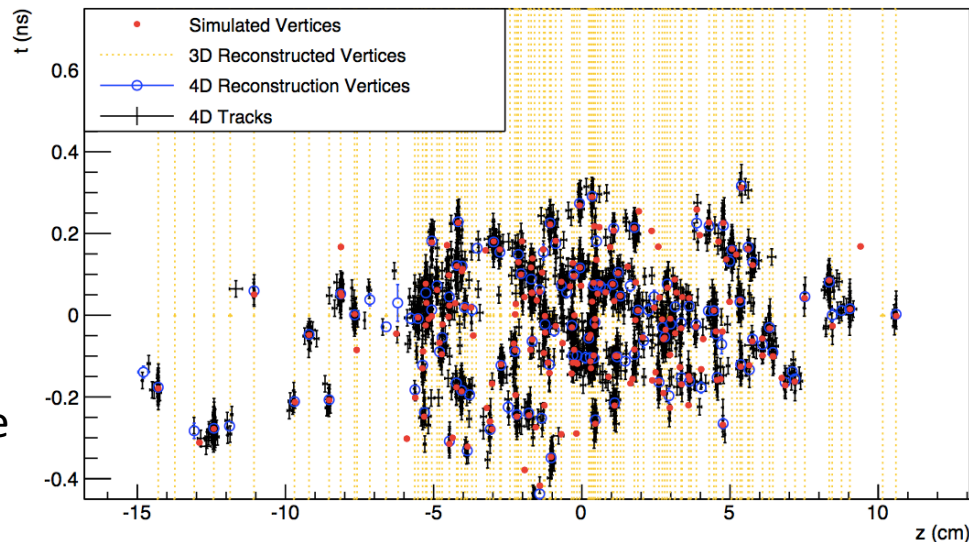


Why a MIP Timing Detector in CMS?

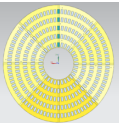
The MTD will provide timing information for MIPs with a 30-40 ps resolution.

Time-tagged charged tracks enable

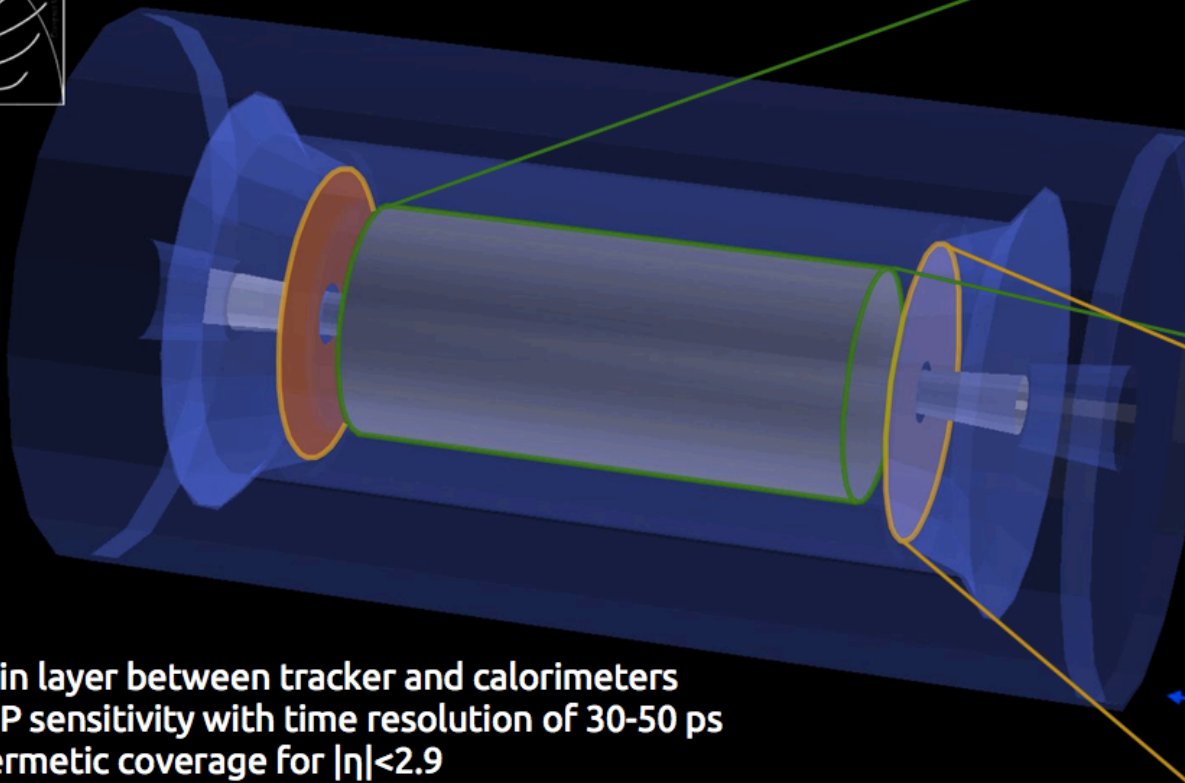
- time compatibility check for track-vertex association
- charged tracks/vertices association with photons and hadronic showers (measured by upgraded calorimeters)
- **Reduction of effective pile-up** to the level of the current CMS detector, exploiting the longitudinal extent of the beams



Interactions are distributed over time (and space) with an RMS of 180-200 ps

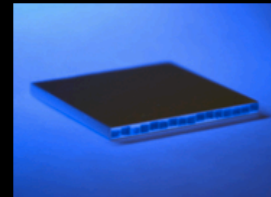
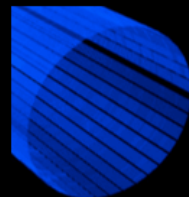


Design of the MTD detector



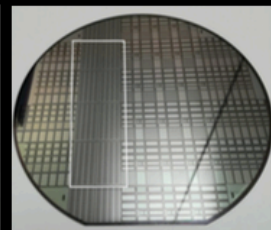
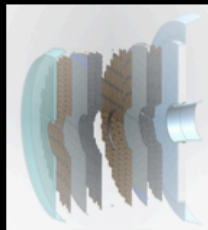
BARREL

Surface $\sim 38 \text{ m}^2$
 Number of channels $\sim 332\text{k}$
 Radiation level $\sim 2 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$
 Sensors: LYSO crystals + SiPMs

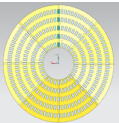


ENDCAPS

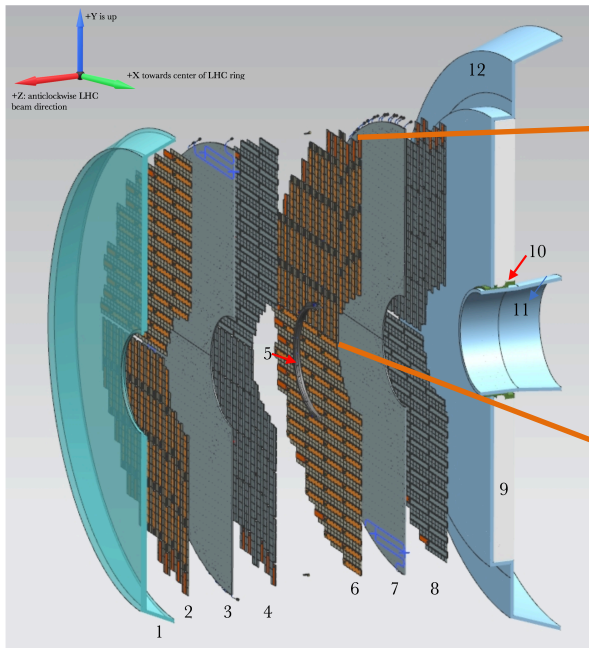
Surface $\sim 7 \text{ m}^2$
 Number of channels $\sim 4000\text{k}$
 Radiation level $\sim 2 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$
 Sensors: Low gain avalanche diodes



- Thin layer between tracker and calorimeters
- MIP sensitivity with time resolution of 30-50 ps
- Hermetic coverage for $|\eta| < 2.9$

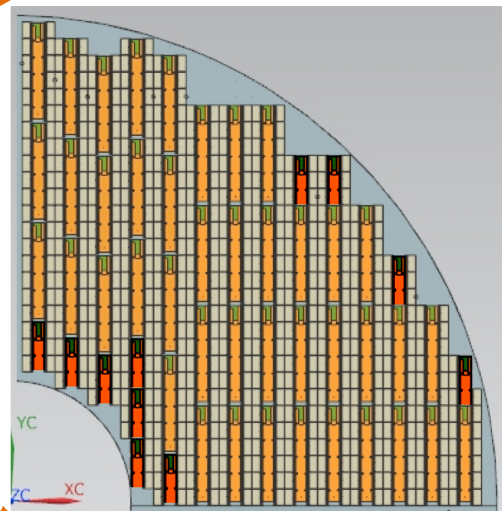


The Endcap Timing Layer (ETL) layout



- 1: ETL Thermal Screen
- 2: Disk 1, Face 1
- 3: Disk 1 Support Plate
- 4: Disk 1, Face 2
- 5: ETL Mounting Bracket
- 6: Disk 2, Face 1
- 7: Disk 2 Support Plate
- 8: Disk 2, Face 2
- 9: HGCal Neutron Moderator
- 10: ETL Support Cone
- 11: Support cone insulation
- 12: HGCal Thermal Screen

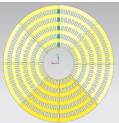
each face made of 4 identical wedges



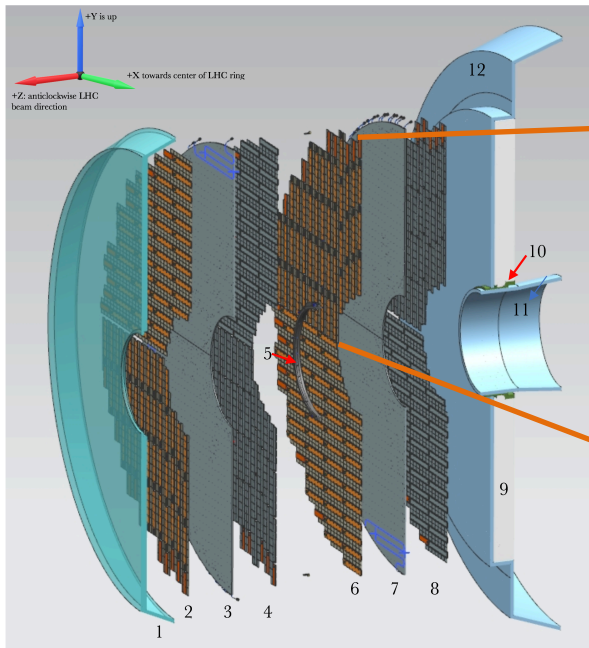
On each endcap side [$|\eta| = 1.6$ to 2.9]

2 supporting disks, with **sensor modules** mounted on **all four faces of the two disks**, placed in an **x-y layout**, in a **staggered way**

(areas for readout, power, and cable infrastructure are covered by the sensors on the opposite face)



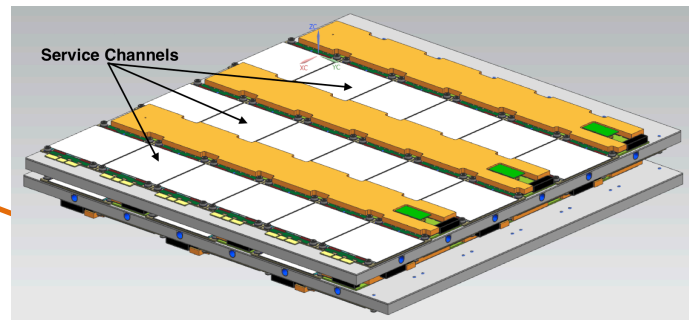
The Endcap Timing Layer (ETL) layout

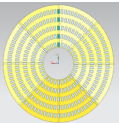


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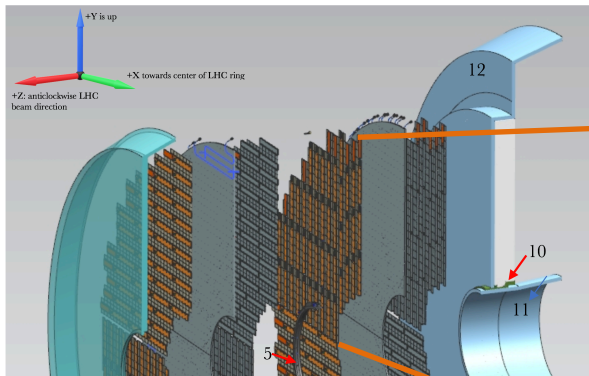


portion of supporting disk with sensors and services





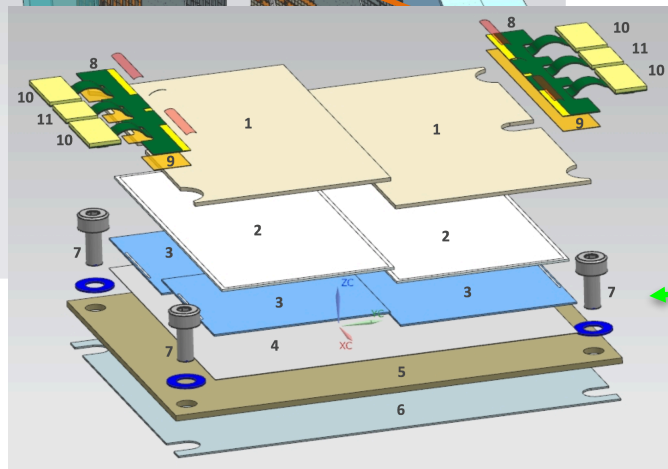
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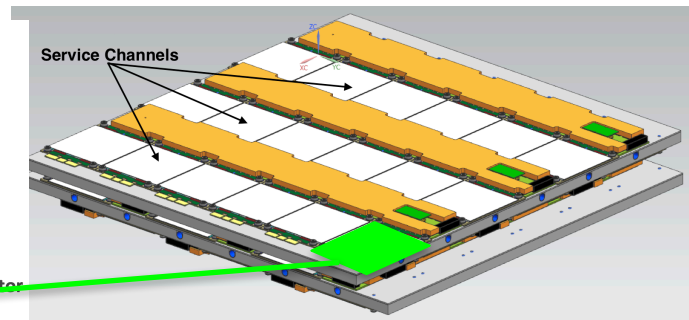
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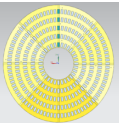


- 1: AIN module cover
- 2: LGAD sensor
- 3: ETL ASIC
- 4: Mounting film
- 5: AIN carrier
- 6: Mounting film
- 7: Mounting screw
- 8: Front-end hybrid
- 9: Adhesive film
- 10: Readout connector
- 11: High voltage connector

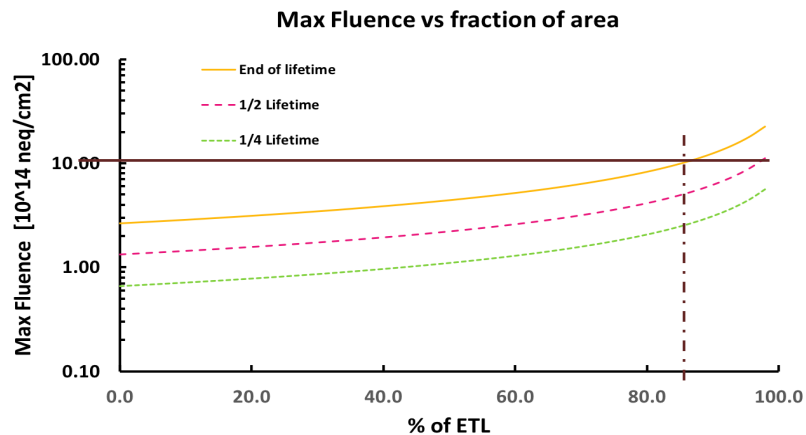
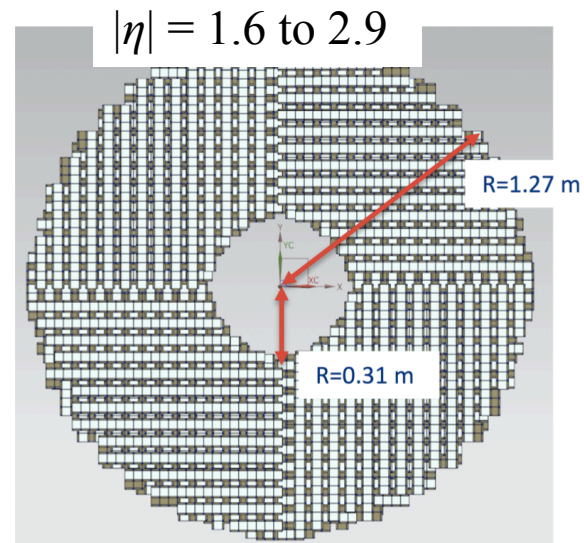
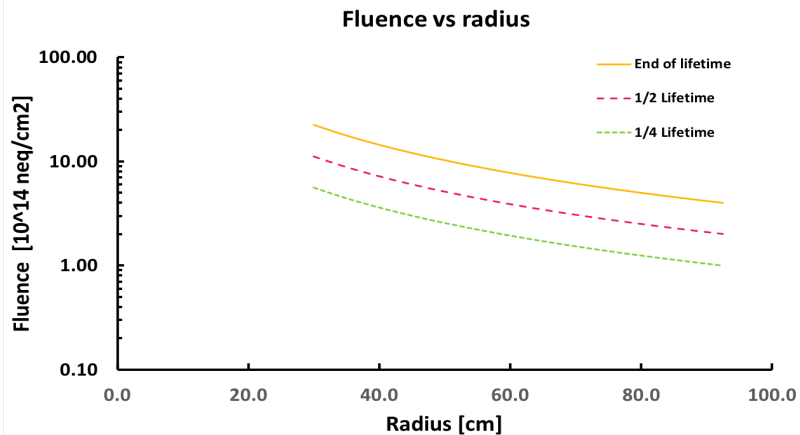


Service Channels

One ETL sensor module, with 2 LGAD sensors read out by 4 ETL ASICs



Expected Irradiation Conditions of ETL

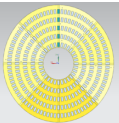


End of lifetime irradiation level (for $\mathcal{L} = 4000 \text{ fb}^{-1}$)

ETL exposure: 42% < $4\text{E}14 \text{ n/cm}^2$

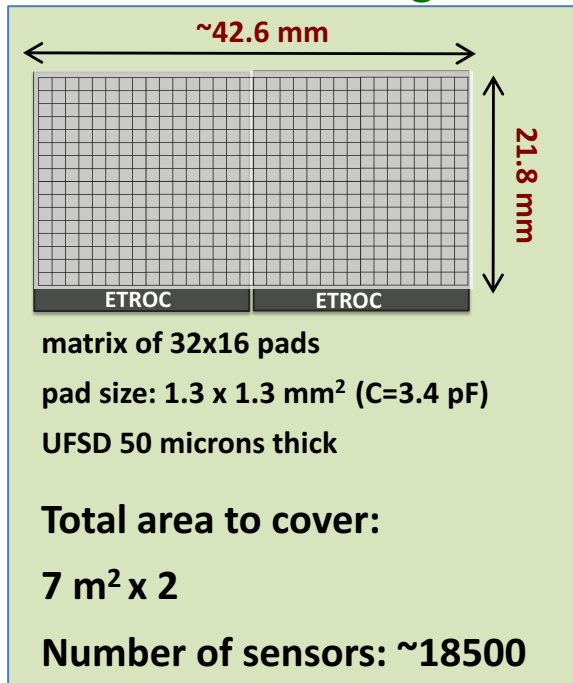
80% < $8\text{E}14 \text{ n/cm}^2$

14% > $1\text{E}15 \text{ n/cm}^2$



The LGAD sensor production/R&D

ETL sensor design



3 VENDORS (FBK, HPK, CNM) engaged in the R&D towards large area UFSDs production (2018) for CMS/ATLAS upgrades, focusing on

Large Area sensor feasibility

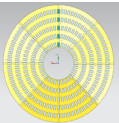
Optimization of gain layer radiation hardness, inter-pad dead spaces, sensor edges, gain uniformity

Long term stability

Evaluate the 35-micron option

Common R&D project with ATLAS

Development work done also in collaboration with RD50



ETL sensor specifications

For radiation damage mitigation, the sensors will be operated at -30°C

Considering the present ETL read-out chip simulation, a time resolution better than ~ 40 ps is achieved for **charges larger than 5 fC** (min Gain = 10)

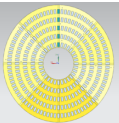
→ sensor needs to provide enough charge, without increasing the noise contribution, till the end of HL-LHC lifetime

When new:

- sensor gain between 10 and 20 in a bias interval between 125V - 175V, with $\text{BD} > 220$ V
- less than $2 \mu\text{A}$ leakage current per mm^2
- Sensor edge < 500 microns, interpad (no-gain) distance < 50 microns
- Gain uniformity within a sensor better than 20%

Low noise, stable operation, and gain above 10 after a fluence of

- $5\text{E}14$ neq/cm^2 for 50% of the total sensors
- $1\text{E}15$ neq/cm^2 for 30% of the total sensors
- $2\text{E}15$ neq/cm^2 for 20% of the total sensors.



2018 R&D SENSOR PRODUCTIONS

FBK, HPK and CNM have delivered their first CMS/ATLAS dedicated R&D productions:

Lot's of results collected so far... some still not final.

**Given their R&D nature, there were unforeseen problems for all the vendors
(either related to the optimizations undertaken, or not ...)**

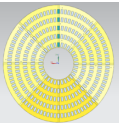
FBK: structures with early breakdown and/or “pop-corn” noise (p-stop design, inter-pad design?)

HPK: the 35microns sensor design suffers very early breakdown (too low bulk resistivity, too high gain layer doping)

CNM: high leakage current/ large variations (inter-pad design ?)

All vendors are “offering” engineering internal productions to address the problems. These productions will be extremely useful for the definition of the characteristics of the next prototyping production this year.

Final Production expected to start in Q1 2023

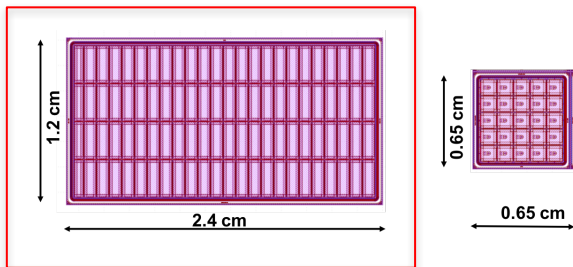


Wafer uniformity and sensor yield

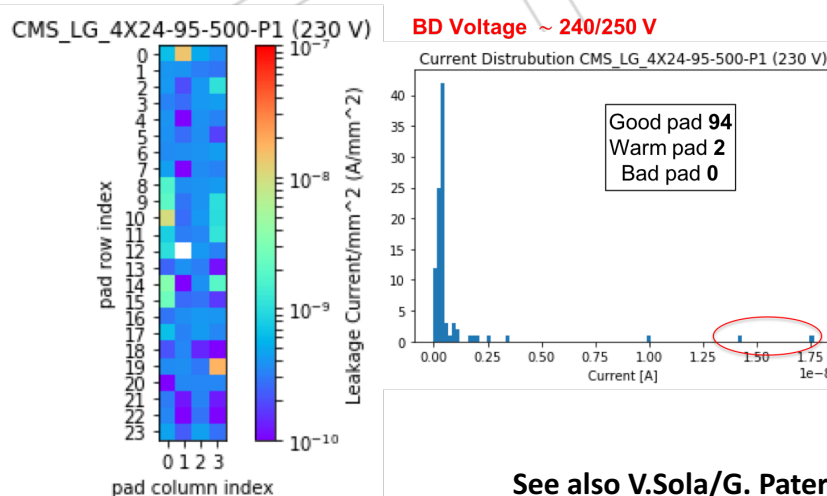
Overall, a very good uniformity and yield from HPK and FBK.

Table 3.4: Summary of the uniformity studies on the latest sensor productions.

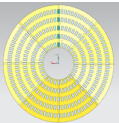
Foundries	Sensor type	# Sensor tested	# Warm pads	# Hot pads	Comments
FBK	4x24 pads	152	14 (0.1%)	0	bias = 100V
FBK	5x5 pads	23	4 (0.7%)	0	bias = 300V
HPK	4x24	15	20 (1.3%)	0	bias = 250V



The largest device present in the 2018 prods, 3.5 times smaller than the final one



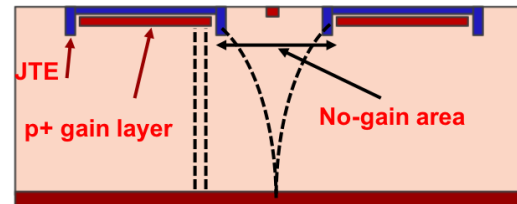
See also V.Sola/G. Paternoster talks

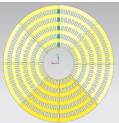


Status of interpad no-gain area

Foundries	No-gain distance [μm]	Comments
CNM	100	The latest production with smaller distances has very high leakage current and cannot be used. A new production is expected in August 2019
FBK	40, 70	In the latest production much smaller distances were attempted but the sensors go into early breakdown. A dedicated new production is expected in April 2019.
HPK	75, 90, 135	Even the shortest separation works well, most likely HPK can obtain even smaller distances.

See also V.Sola/G. Paternoster talks

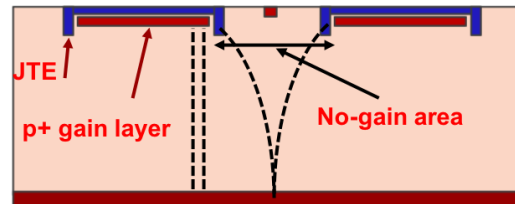




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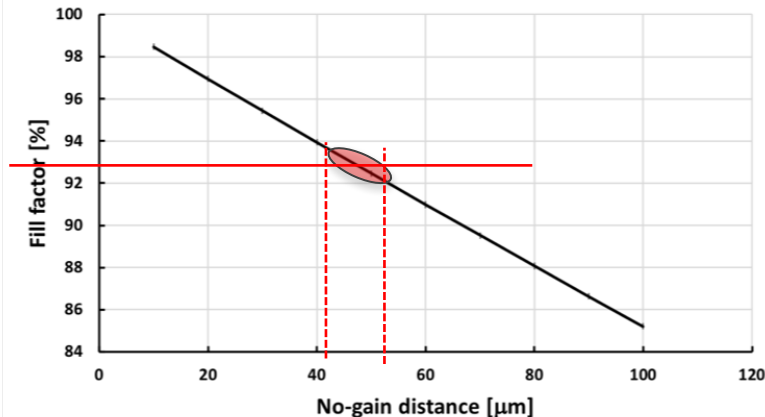


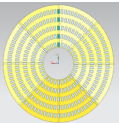
Our goal is to have a fill factor of 85% per layer, for a final average 1.8 hits per track

- 5% comes from the sensors placement
- 2-3 % dead area comes from the butting of sensors in the module
- 7-8% comes from the no-gain area

...Not yet achieved

Fill factor vs no-gain distance for a 1.3 x 1.3 mm² pad



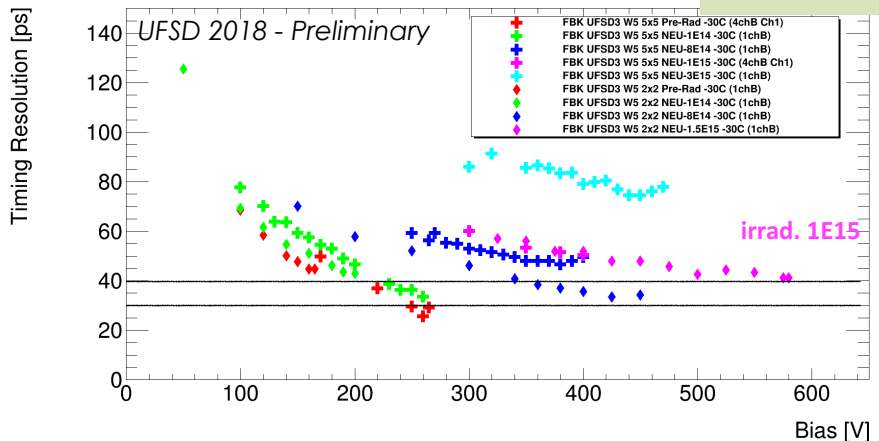
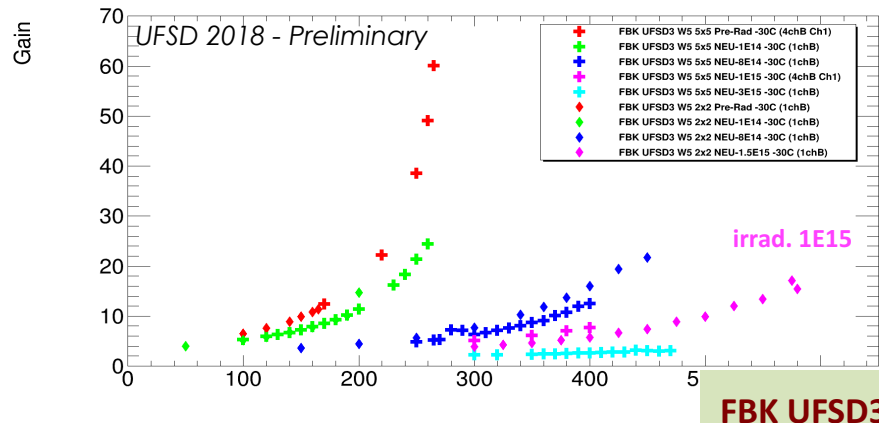
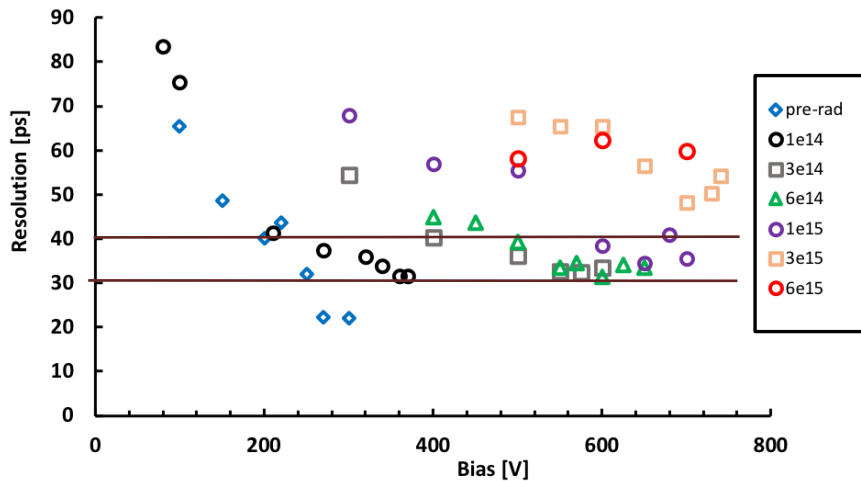


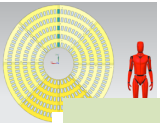
Time Resolution (beta source lab tests)

See Stefan Guindon talk for time resolution performances of CNM and preliminary results on HPK Type3.1

HPK 50D

HPK 50D Resolution CFD20 -20C

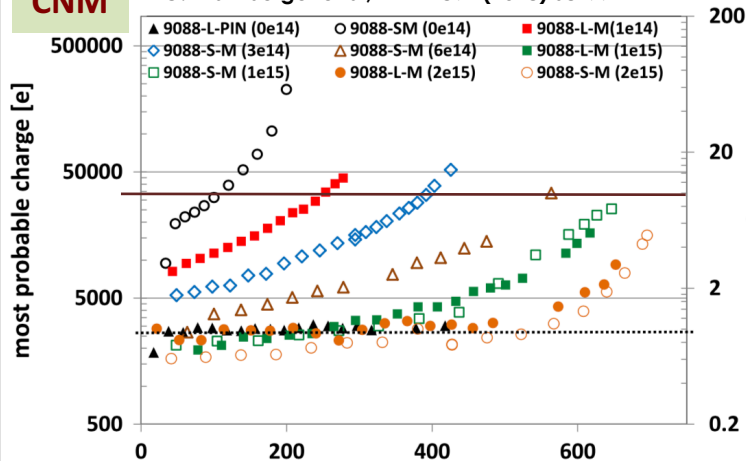




On radiation hardness...

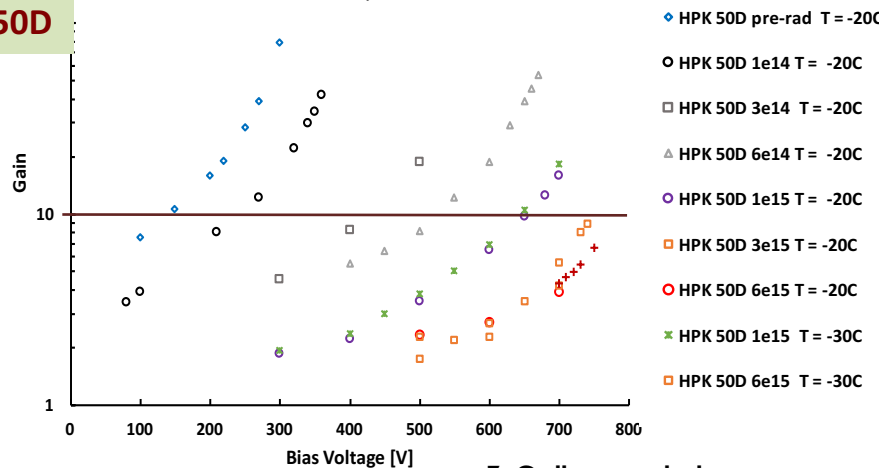
CNM

G. Kramberger et al, NIMA 891 (2018) 68-77



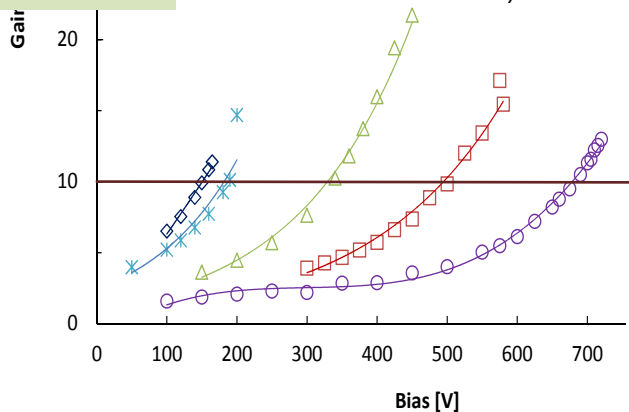
HPK 50D

Gain vs. Bias, $T = -20\text{ }^\circ\text{C}$ & $T = -30\text{ }^\circ\text{C}$



FBK UFSD3

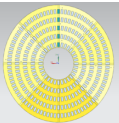
UFSD 2018 - Preliminary



- ◇ FBK UFSD3 W5 2x2 Array PreRad - 30C (Single Channel)
- × FBK UFSD3 W5 2x2 Array NEU 1E14 -30C (Single Channel)
- △ FBK UFSD3 W5 2x2 Array NEU 8E14 -30C (Single Channel)
- FBK UFSD3 W5 2x2 Array NEU 1.5E15 -30C (Single Channel)
- FBK UFSD3 W5 2x2 Array NEU 3E15 -30C (Single Channel)

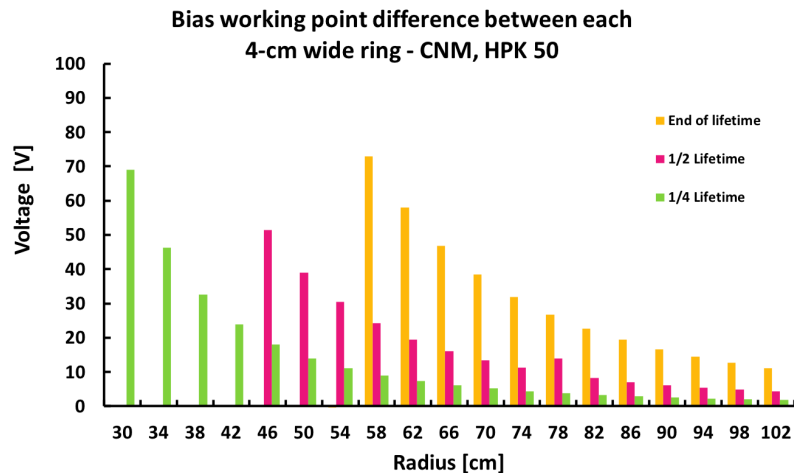
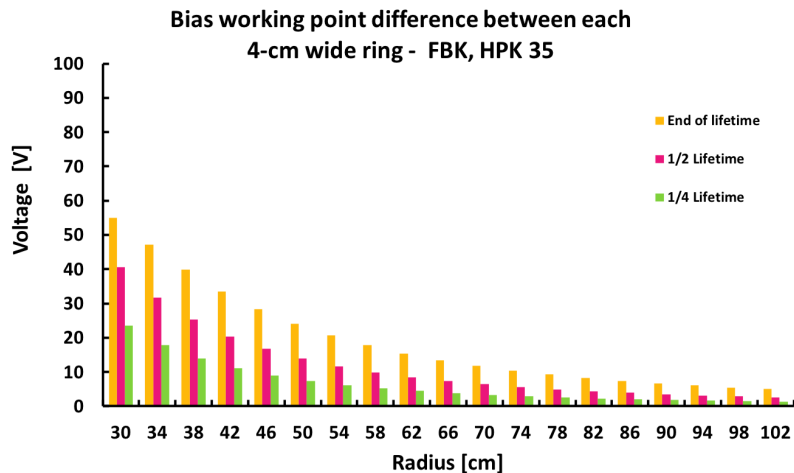
Z. Galloway et al.,

<https://arxiv.org/abs/1707.04961>



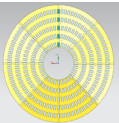
On the detector sensor biasing schema

Comparison between the best devices of the three vendors so far:



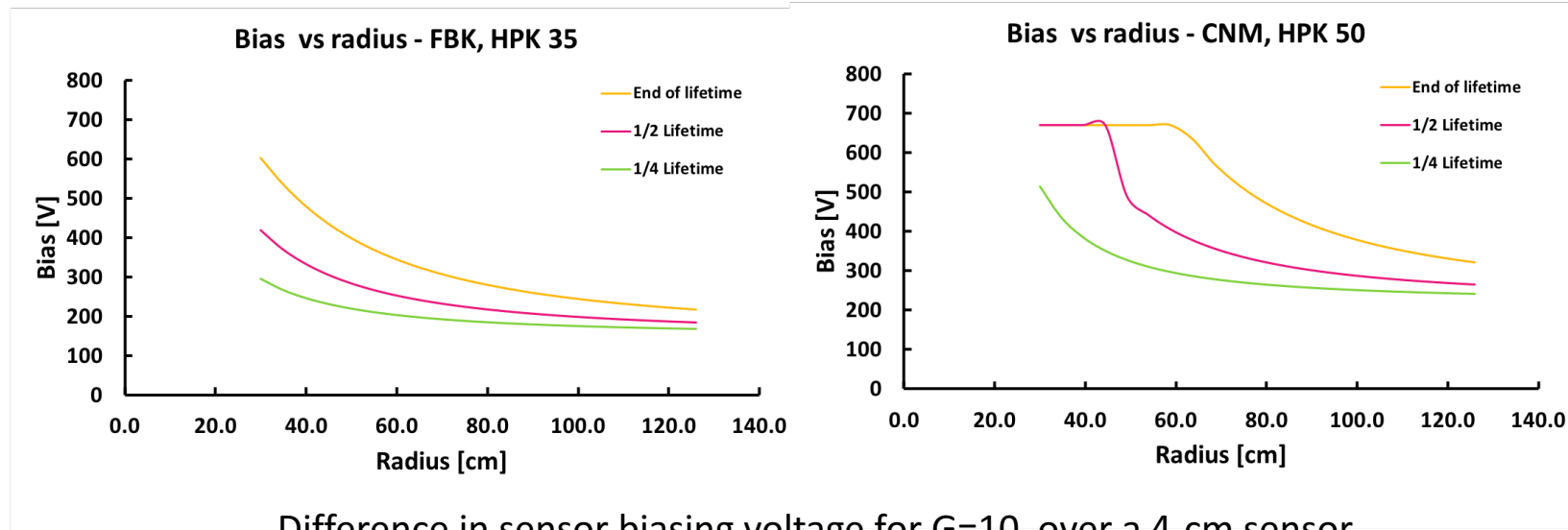
Difference in sensor biasing voltage for $G=10$ over a 4-cm sensor,
as a function of ETL radius, for three different moment in CMS lifetime.

The sensor edge at higher rapidity would require higher bias, so it will be under-biased to prevent breakdown at the sensor edge at lower rapidity.



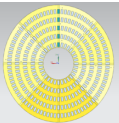
On the detector sensor biasing schema

Bias point for a Gain=10 sensor as a function of ETL radius



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Conclusions

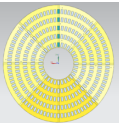
Both CMS and ATLAS need to build large area timing detectors using UFSD sensors of $\sim 8\text{-}9\text{ cm}^2$. Common R&D project!

CNM, FBK and HPK are engaged in this R&D, and it is progressing well:

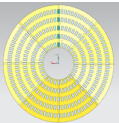
- The yield for large area sensors (measured now in FBK, HPK) is very high
- The radiation hardness has improved: latest FBK can reach good gain above $1.5\text{E}15\text{ n}_{\text{eq}}/\text{cm}^2$.
- The sensors tested in lab can reach a time resolution better than 40 ps

Stay tuned! a new round of prototyping production will be available in 2019.

NB: writing the MTD TDR, to be submitted to LHCC by the end of March.



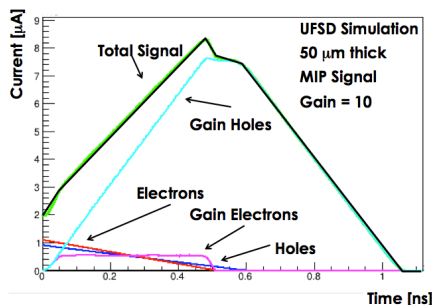
BACKUP



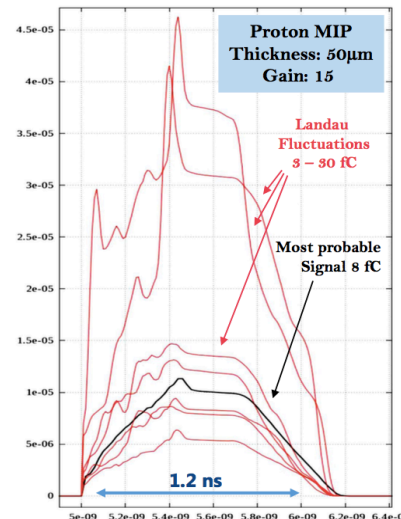
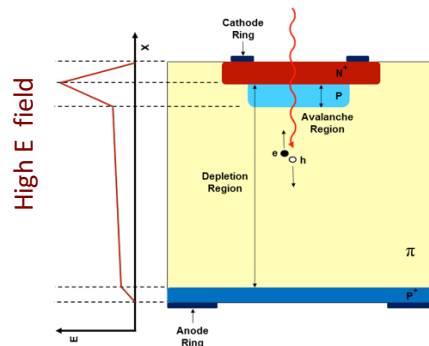
Ultra Fast Silicon Detectors

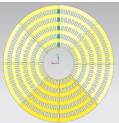
LGAD (Low Gain Avalanche Diodes) technology sensors optimized for timing measurements

The idea: add a thin layer of doping to produce low controlled multiplication (the gain layer)



The main contribution to the signal comes from gain holes.
The signal shape depends on the sensor thickness and gain

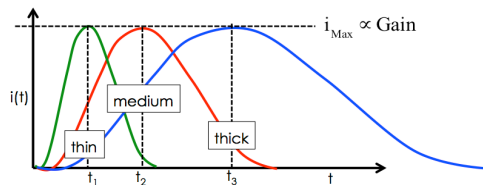




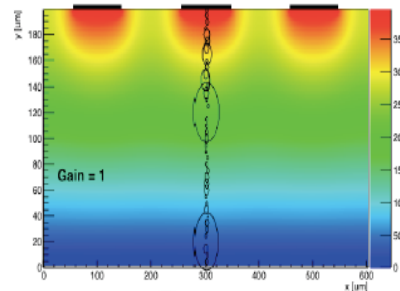
How do we measure the time

$$\sigma_{\text{Jitter}} \approx N/(dV/dt) \approx t_{\text{rise}}/(S/N)$$

- need **gain** to increase S
- need **thin detector** to decrease t_{rise}



Non uniform charge deposition
Decreases with detector thickness



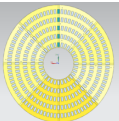
$$\sigma_t^2 = \sigma_{\text{Jitter}}^2 + \sigma_{\text{Time Walk}}^2 + \sigma_{\text{Landau Noise}}^2 + \sigma_{\text{Distortion}}^2 + \sigma_{\text{TDC}}^2$$

Minimized by
correction
techniques

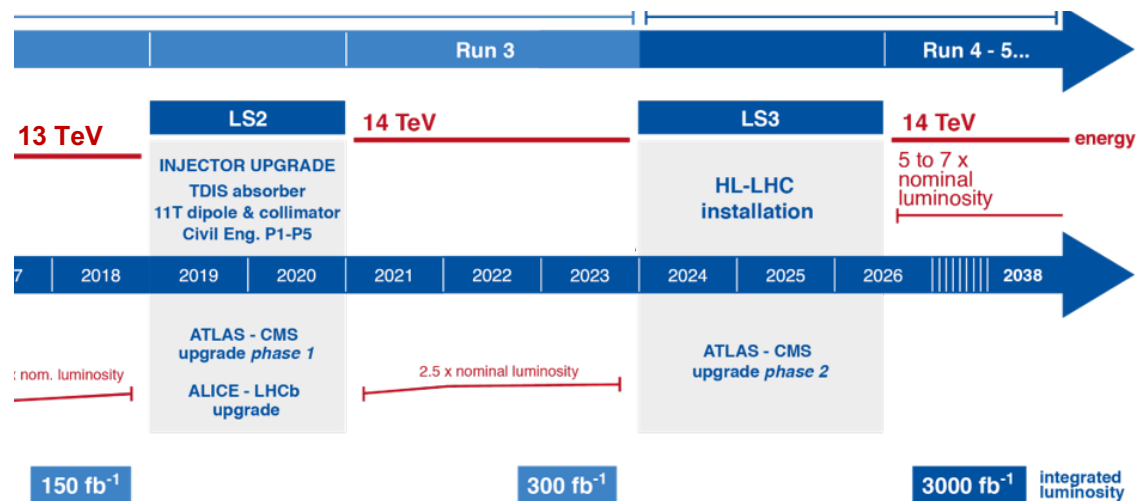
Minimized by
optimized RO
electronics

$$I_{\text{Ramo}} \approx q v_{\text{drift}} E_w$$

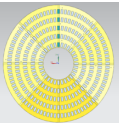
Requires **uniform** v_{drift} and E_w



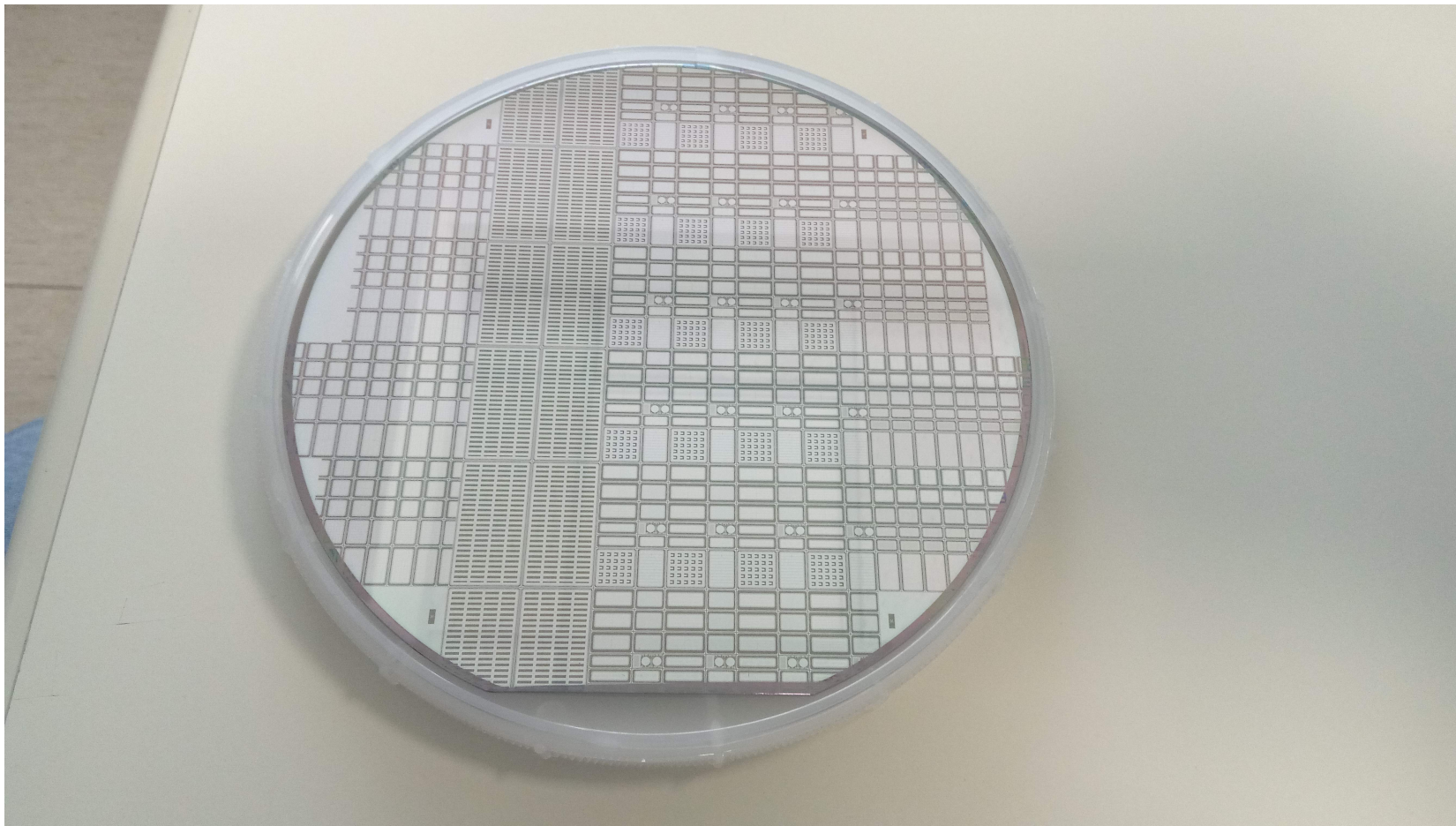
LHC upgrade: the High Luminosity Challenge

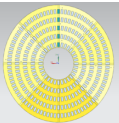


	Inst. Lumi (cm ⁻² s ⁻¹)	Peak pileup (PU)	Int. Lumi (fb ⁻¹ /y)	Hadron fluence (particles/cm ²)
LHC	1.7 x 10 ³⁴	60	40-50	12E11 η =1 ; 3E13 η =2.6
HL-LHC	5-7.5 x 10 ³⁴	140-200	250-320	7.6E12 η =1 ; 2E14 η =2.6

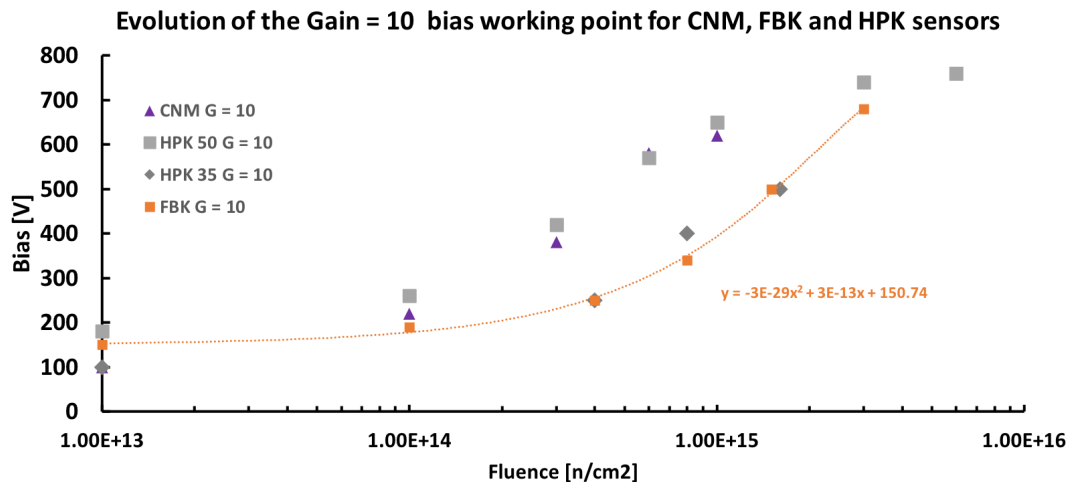


UFSD3 wafer layout





Bias for Gain = 10 vs fluence



- Carbon reduces the HV values needed at a given fluence
- The “**voltage reach**” of the detectors: sensors should hold high bias since it **extends the possibility to go to higher fluences.**